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a curing temperature over said semiconductor wafer so as to cover said main surface;  
heating and curing said sheet encapsulating material by a heating apparatus to  
thereby form an encapsulating resin layer;  
polishing said encapsulating resin layer to expose portions of said plurality of  
bumps; and  
dividing said semiconductor wafer into individual semiconductor device chips.

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3. (Amended) The method as claimed in claim 1, further comprising:  
forming external terminals each having conductivity so as to be connected to  
said bumps respectively.

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7. (Amended) The method as claimed in claim 1, wherein said heating and curing  
are done in such a manner that the heating of said sheet encapsulating material is at a  
temperature lower than the curing temperature of said sheet encapsulating material, and  
at which the viscosity of said sheet encapsulating material is kept low, and said sheet  
encapsulating material is kept for a predetermined time at a temperature at which voids  
contained in said sheet encapsulating material are easy to be eliminated, and thereafter  
said sheet encapsulating material is increased in temperature to said curing temperature  
or higher.

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8. (Amended) The method as claimed in claim 1, wherein said heating and curing  
are done in such a manner that the heating of said sheet encapsulating material is at a  
temperature lower than the curing temperature of said sheet encapsulating material, and  
at which the viscosity of said sheet encapsulated material is kept low, and said sheet  
encapsulating material is kept for a predetermined time at a reduced pressure at a  
temperature at which voids contained in said sheet encapsulating material is easy to be  
eliminated, and thereafter said sheet encapsulating material is increased in temperature  
to said curing temperature or higher.

9. (Amended) The method as claimed in claim 1, wherein said heating and curing  
are done in such a manner that the heating of said sheet encapsulated material is at a

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temperature lower than the curing temperature of said sheet encapsulating material, and at which the viscosity of said sheet encapsulating material is kept low, and said sheet encapsulated material is kept for a first predetermined time under a first reduced pressure at a void removal temperature at which voids contained in said sheet encapsulating material are easy to be eliminated, and thereafter repeatedly held plural times for a second predetermined time while being kept at the void removal temperature at a second reduced pressure between the first reduced pressure and atmospheric pressure, and thereafter said sheet encapsulated material is increased in temperature to the curing temperature or higher.